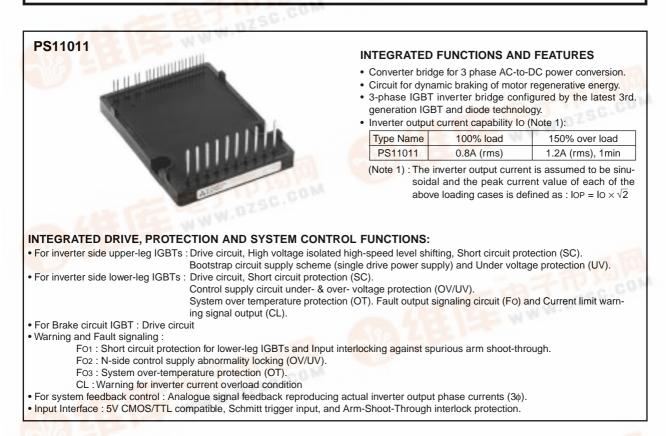
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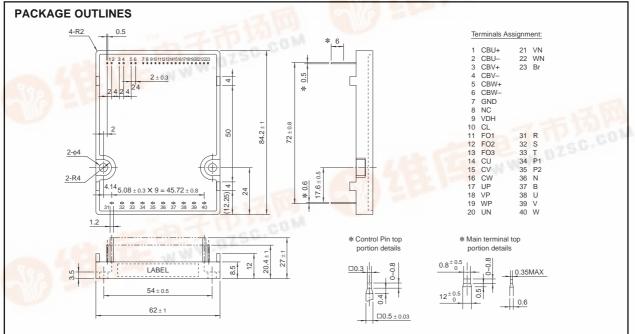
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APPLICATION

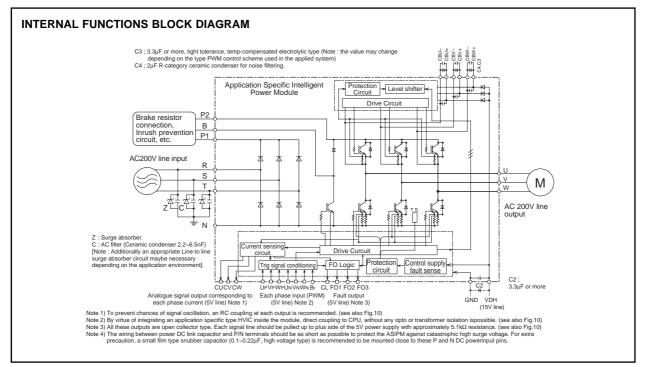
Acoustic noise-less 0.1kW/AC200V class 3 phase inverter and other motor control applications





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(Fig. 2)

MAXIMUM RATINGS (Tj = 25°C) INVERTER PART (Including Brake Part)

Symbol	Item	Condition	Ratings	Unit
Vcc	Supply voltage	Applied between P2-N	450	V
VCC(surge)	Supply voltage (surge)	Applied between P2-N, Surge-value	500	V
VP or VN	Each output IGBT collector-emitter static voltage	Applied between P-U, V, W, Br or U, V, W, Br-N	600	V
VP(S) or VN(S)	Each output IGBT collector-emitter switching surge voltage	Applied between P-U, V, W, Br or U, V, W, Br-N	600	V
±IC(±ICP)	Each output IGBT collector current	Tc = 25°C	±2 (±4)	A
IC(ICP)	Brake IGBT collector current		2 (4)	Α
IF(IFP)	Brake diode anode current	Note: "()" means IC peak value	2 (4)	Α

CONVERTER PART

Symbol	Item	Condition	Ratings	Unit
Vrrm	Repetitive peak reverse voltage		800	V
Ea	Recommended AC input voltage		220	V
lo	DC output current	36 rectifying circuit	25	А
IFSM	Surge (non-repetitive) forward current	1 cycle at 60Hz, peak value non-repetitive	138	Α
l ² t	I ² t for fusing	Value for one cycle of surge current	80	A ² s

CONTROL PART

Symbol	Item	Condition	Ratings	Unit
Vdh, Vdb	Supply voltage	Applied between VDH-GND, CBU+-CBU-, CBV+-CBV-, CBW+-CBW-	20	V
VCIN	Input signal voltage	Applied between UP \cdot VP \cdot WP \cdot UN \cdot VN \cdot WN \cdot Br-GND	-0.5 ~ 7.5	V
Vfo	Fault output supply voltage	Applied between F01 · F02 · F03-GND	-0.5 ~ 7	V
lfo	Fault output current	Sink current of F01 · F02 · F03	15	mA
VCL	Current-limit warning (CL) output voltage	Applied between CL-GND	-0.5 ~ 7	V
ICL	CL output current	Sink current of CL	15	mA
Ico	Analogue current signal output current	Sink current of CU · CV · CW	±1	mA



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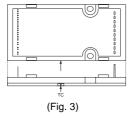
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TOTAL SYSTEM

Symbol	Item	Condition	Ratings	Unit
Tj	Junction temperature	(Note 2)	-20 ~ +125	°C
Tstg	Storage temperature	—	-40 ~ +125	°C
Тс	Module case operating temperature	(Fig. 3)	-20 ~ +100	°C
Viso	Isolation voltage	60 Hz sinusoidal AC applied between all terminals and the base plate for 1 minute.	2500	Vrms
_	Mounting torque	Mounting screw: M3.5	0.78 ~ 1.27	kg⋅cm

Note 2) The item defines the maximum junction temperature for the power elements (IGBT/Diode) of the ASIPM to ensure safe operation. However, these power elements can endure junction temperature as high as 150°C instantaneously. To make use of this additional temperature allowance, a detailed study of the exact application conditions is required and, accordingly, necessary information is requested to be provided before use.

CASE TEMPERATURE MEASUREMENT POINT (3mm from the base surface)



THERMAL RESISTANCE

Symbol	Item	Condition	Ratings			L lm it
			Min.	Тур.	Max.	Unit
Rth(j-c)Q	Junction to case Thermal Resistance	Inverter IGBT (1/6)	—	—	7.3	°C/W
Rth(j-c)F		Inverter FWDi (1/6)	—	—	6.1	°C/W
Rth(j-c)QB		Brake IGBT	_	_	7.3	°C/W
Rth(j-c)FB		Brake FWDi	—	—	6.1	°C/W
Rth(j-c)FR		Converter Di (1/6)	_	—	4.8	°C/W
Rth(c-f)	Contact Thermal Resistance	Case to fin, thermal grease applied (1 Module)	_	_	0.053	°C/W

ELECTRICAL CHARACTERISTICS (Tj = 25°C, VDH = 15V, VDB = 15V unless otherwise noted)

Symbol	Item	Condition	Ratings			11-14
Symbol			Min.	Тур.	Max.	Unit
VCE(sat)	Collector-emitter saturation voltage	VDH = VDB = 15V, Input = ON, Tj = 25°C, IC = 2A	—	_	2.9	V
VEC	FWDi forward voltage	Tj = 25° C, IC = $-2A$, Input = OFF	—	—	2.9	V
VCE(sat)Br	Brake IGBT Collector-emitter saturation voltage	VDH = 15V, Input = ON, Tj = 25°C, IC = 2A	_	_	3.5	V
VFBr	Brake diode forward voltage	Tj = 25° C, IF = 2A, Input = OFF	—	—	2.9	V
Irrm	Converter diode reverse current	VR = VRRM, Tj = 125°C	—	—	8	mA
Vfr	Converter diode voltage	Tj = 25°C, IF = 5A	-	—	1.5	V
ton	- Switching times	1/2 Bridge inductive load, Input = ON	0.3	0.6	1.5	μs
tc(on)		Vcc = 300V, lc = 2A, Tj = 125°C	_	0.2	0.6	μs
toff		VDH = 15V, VDB = 15V	—	1.1	1.8	μs
tc(off)		Note : ton, toff include delay time of the internal control	_	0.35	1.0	μs
trr	FWD reverse recovery time	circuit	—	0.1	—	μs
	Short circuit endurance	Vcc ≤ 400V, Input = ON (one-shot)	No destruction Fo output by protection operation			
	(Output, Arm, and Load,	Tj = 125°C start			ration	
	Short Circuit Modes)	$13.5V \le VDH = VDB \le 16.5V$				
		$VCC \le 400V$, $Tj \le 125^{\circ}C$,	 No destruction No protecting operation No Fo output 			
	Switching SOA	Ic < IOL(CL) operation level, Input = ON				
		$13.5V \le VDH = VDB \le 16.5V$				



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Ratings Symbol Item Condition Unit Min. Max. Тур. Idн VDH = 15V, VCIN = 5V mΑ Circuit current 150 Vth(on) Input on threshold voltage 0.8 V 1.4 2.0 Vth(off) Input off threshold voltage 2.5 3.0 4.0 V Ri Integrated between input terminal-VDH 150 kΩ Input pull-up resistor PWM input frequency fpwM $TC \le 100^{\circ}C, Tj \le 125^{\circ}C$ 2 20 kHz txx $VDH = 15V, TC = -20^{\circ}C \sim +100^{\circ}C$ (Note 3) 1 500 μs Allowable input on-pulse width Allowable input signal dead time for Relates to corresponding input 2.2 tdead us _ ____ blocking arm shoot-through (Except brake part) TC = -20°C ~ +100°C 65 100 Input inter-lock sensing ns tint Relates to corresponding input (Except brake part) _ 1.87 2.27 2.57 Vco Ic = 0AV VDH = 15VAnalogue signal linearity with 0.77 1.47 Vc+(200%) Ic = IOP(200%) $TC = -20^{\circ}C \sim +100^{\circ}C$ 1.17 V output current 2.97 3.37 3.67 Vc-(200%) Ic = -IOP(200%)(Fig. 4) V |∆Vco| Offset change area vs temperature VDH = 15V, TC = -20°C ~ +100°C 15 m٧ 0.7 VC+ Ic > IOP(200%), VDH = 15V V Analogue signal output voltage limit Vc-(Fig. 4) 4.0 V Analogue signal over all linear variation |Vco-Vc±(200%)| 1.1 V ΔVc(200%) Correspond to max. 500µs data hold period rсн Analogue signal data hold accuracy -5 5 % (Fig. 5) only, Ic = IOP(200%) (Fig. 8) 3 td(read) Analogue signal reading time After input signal trigger point us ±IOL (Note 4) 2.64 3.10 3.60 Current limit warning (CL) operation level VDH =15V, TC = -20°C ~ +100°C A ICL(H) Signal output current of Idle 1 μA Open collector output CL operation 1 ICL(L) Active mΑ SC Short circuit over current trip level Tj = 25°C (Fig. 7) (Note 5) 6.00 9.60 3.50 A OT Trip level 100 110 120 °C Over temperature protection VDH =15V OTr Reset level 90 °C UVdh Trip level 11.05 12.00 12.75 V UVDH Reset level 12.50 V 11.55 13.25 OVDH Trip level 18.00 19.20 20.15 V $TC = -20^{\circ}C \sim +100^{\circ}C$ Supply circuit under & OVDH Reset level 16.50 17.50 18.65 V over voltage protection Tj ≤ 125°C UVdb Trip level V 10.0 11.0 12.0 Reset level UVDBr 10.5 11.5 12.5 V Filter time us td∨ _ 10 Idle μΑ IFO(H) _ 1 Fault output current Open collector output Active IFO(L) 1 mA

ELECTRICAL CHARACTERISTICS (Tj = 25°C, VDH = 15V, VDB = 15V unless otherwise noted)

(Note 3) : (a) Allowable minimum input on-pulse width : This item applies to P-side circuit only.

(b) Allowable maximum input on-pulse width : This item applies to both P-side and N-side circuits excluding the brake circuit.

(Note4): CL output : The "current limit warning (CL) operation circuit outputs warning signal whenever the arm current exceeds this limit. The circuit is reset automatically by the next input signal and thus, it operates on a pulse-by-pulse scheme.

(Note5): The short circuit protection works instantaneously when a high short circuit current flows through an internal IGBT rising up momentarily. The protection function is, thus meant primarily to protect the ASIPM against short circuit distraction. Therefore, this function is not recommended to be used for any system load current regulation or any over load control as this might, cause a failure due to excessive temperature rise. Instead, the analogue current output feature or the over load warning feature (CL) should be appropriately used for such current regulation or over load control operation. In other words, the PWM signals to the ASIPM should be shut down, in principle, and not to be restarted before the junction temperature would recover to normal, as soon as a fault is feed back from its Fo1 pin of the ASIPM indicating a short circuit situation.

RECOMMENDED CONDITIONS

Symbol	Item	Condition	Ratings	Unit
Vcc	Supply voltage	Applied across P2-N terminals	400 (max.)	V
Vdh, Vdb	Control supply voltage	Applied between VDH-GND, CBU+-CBU-, CBV+-CBV-, CBW+-CBW-	15±1.5	V
ΔV DH, ΔV DB	Supply voltage ripple		±1 (max.)	V/µs
VCIN(on)	Input on voltage		0 ~ 0.3	V
VCIN(off)	Input off voltage		4.8 ~ 5.0	V
fpwm	PWM Input frequency	Using application circuit	2 ~ 20	kHz
tdead	Arm shoot-through blocking time	Using application circuit	2.2 (min.)	μs



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Fig. 4 OUTPUT CURRENT ANALOGUE SIGNALING LINEARITY

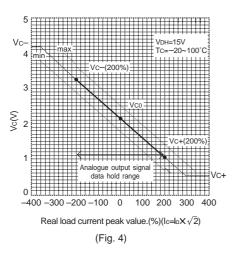
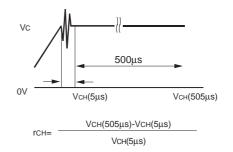
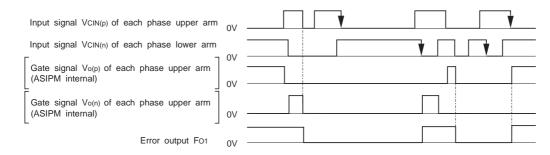


Fig. 5 OUTPUT CURRENT ANALOGUE SIGNALING "DATA HOLD" DEFINITION



Note ; Ringing happens around the point where the signal output voltage changes state from "analogue" to "data hold" due to test circuit arrangement and instrumentational trouble. Therefore, the rate of change is measured at a 5 μs delayed point.

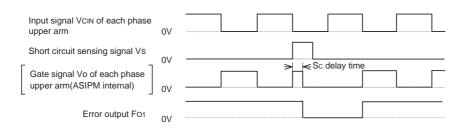
Fig. 6 INPUT INTERLOCK OPERATION TIMING CHART



Note : Input interlock protection circuit ; It is operated when the input signals for any upper-arm / lower-arm pair of a phase are simultaneously in "LOW" level.

By this interlocking, both upper and lower IGBTs of this mal-triggered phase are cut off, and "Fo" signal is outputted. After an "input interlock" operation the circuit is latched. The "Fo" is reset by the high-to-low going edge of either an upper-leg, or a lower-leg input, whichever comes in later.

Fig. 7 TIMING CHART AND SHORT CIRCUIT PROTECTION OPERATION



Note : Short circuit protection operation. The protection operates with "Fo" flag and reset on a pulse-by-pulse scheme. The protection by gate shutdown is given only to the IGBT that senses an overload (excluding the IGBT for the "Brake").



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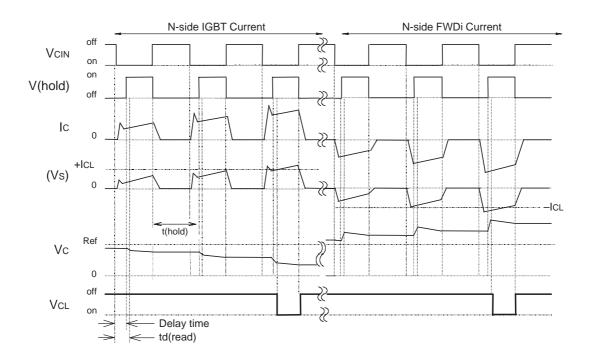
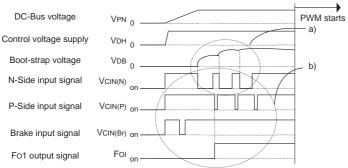


Fig. 8 INVERTER OUTPUT ANALOGUE CURRENT SENSING AND SIGNALING TIMING CHART

Fig. 9 START-UP SEQUENCE

Normally at start-up, Fo and CL output signals will be pulled-up High to Supply voltage (OFF level); however, Fo1 output may fall to Low (ON) level at the instant of the first ON input pulse to an N-Side IGBT. This can happen particularly when the boot-strap capacitor is of large size. Fo1 resetting sequence (together with the boot-strap charging sequence) is explained in the following graph



a) Boot-strap charging scheme :

Apply a train of short ON pulses at all N-IGBT input pins for adequate charging (pulse width = approx. 20μs number of pulses =10 ~ 500 depending on the boot-strap capacitor size)

b) Fo1 resetting sequence:

Apply ON signals to the following input pins : Br \rightarrow Un/Vn/Wn \rightarrow Up/Vp/Wp in that order.

Fig. 10 RECOMMENDED I/O INTERFACE CIRCUIT

